NSN 5961-01-092-4367

Transistor - Page 1 of 1



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Inclosure Material:

Metal

Overall Length:

Between 0.250 inches and 0.300 inches

Overall Diameter:

Between 0.760 inches and 0.830 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

500.0 breakdown voltage, collector to emitter, sustained and 700.0 breakdown voltage, collector to emitter, with specified voltage

between base and emitter and 8.0 $\,$ emitter to base voltage, $\,$ dc $\,$

Current Rating Per Characteristic:

Between 10.00 amperes source cutoff current and 50.00 amperes source cutoff current

Power Rating Per Characteristic:

250.0 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Terminal Type And Quantity:

1 case and 2 pin

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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